Preliminary Amendment

Applicant: Recai Sezi et al.

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Title: SEMICONDUCTOR ARRANGEMENT WITH NON-VOLATILE MEMORIES

IN THE ABSTRACT

Please replace the Abstract with the following rewritten paragraph:

SEMICONDUCTOR ARRANGEMENT WITH NONVOLATILE MEMORIES

Abstract

Semiconductor arrangement-having nonvolatile memories

One aspect of the The-invention relates to a semiconductor arrangement having at least one nonvolatile memory cell which has a first electrode comprising at least two layers; and having an organic material, the organic material forming a compound with that layer of the first electrode which is in direct contact. Fone aspect of the invention furthermore relates to a method for producing the nonvolatile memory cell, a semiconductor arrangement having a plurality of memory cells according to the invention, and a method for producing the same.